# **Power MOSFET**

# 40 V, 0.7 m $\Omega$ , 378 A, Single N-Channel

#### **Features**

- Small Footprint (5x6 mm) for Compact Design
- Low R<sub>DS(on)</sub> to Minimize Conduction Losses
- Low Q<sub>G</sub> and Capacitance to Minimize Driver Losses
- NVMFS5C404NWF Wettable Flank Option for Enhanced Optical Inspection
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

## MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			$V_{DSS}$	40	V
Gate-to-Source Voltage			$V_{GS}$	±20	V
Continuous Drain		T <sub>C</sub> = 25°C	I <sub>D</sub>	378	Α
Current R <sub>θJC</sub> (Notes 1, 3)	Steady	T <sub>C</sub> = 100°C		267	
Power Dissipation	State	T <sub>C</sub> = 25°C	$P_{D}$	200	W
R <sub>θJC</sub> (Note 1)		T <sub>C</sub> = 100°C		100	
Continuous Drain		$T_A = 25^{\circ}C$	I <sub>D</sub>	53	Α
Current R <sub>θJA</sub> (Notes 1, 2, 3)	Steady	T <sub>A</sub> = 100°C		37	
Power Dissipation	State	T <sub>A</sub> = 25°C	$P_{D}$	3.9	W
R <sub>θJA</sub> (Notes 1 & 2)		T <sub>A</sub> = 100°C		1.9	
Pulsed Drain Current	$T_A = 25^{\circ}C, t_p = 10 \mu s$		I <sub>DM</sub>	900	Α
Operating Junction and Storage Temperature			T <sub>J</sub> , T <sub>stg</sub>	-55 to + 175	°C
Source Current (Body Diode)			I <sub>S</sub>	191	Α
Single Pulse Drain-to-Source Avalanche Energy (I <sub>L(pk)</sub> = 38 A)		E <sub>AS</sub>	907	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case - Steady State	$R_{\theta JC}$	0.75	°C/W
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	39	

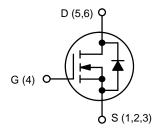
- The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
- 2. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
- 3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



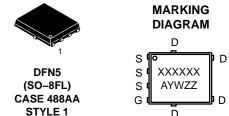
#### ON Semiconductor®

#### www.onsemi.com

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D</sub> MAX
40 V	$0.7~\mathrm{m}\Omega$ @ 10 V	378 A



**N-CHANNEL MOSFET** 



XXXXXX = 5C404N

(NVMFS5C404N) or

404NWF

(NVMFS5C404NWF) = Assembly Location

= Year

W = Work Week

= Lot Traceability

#### ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

# **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise specified)

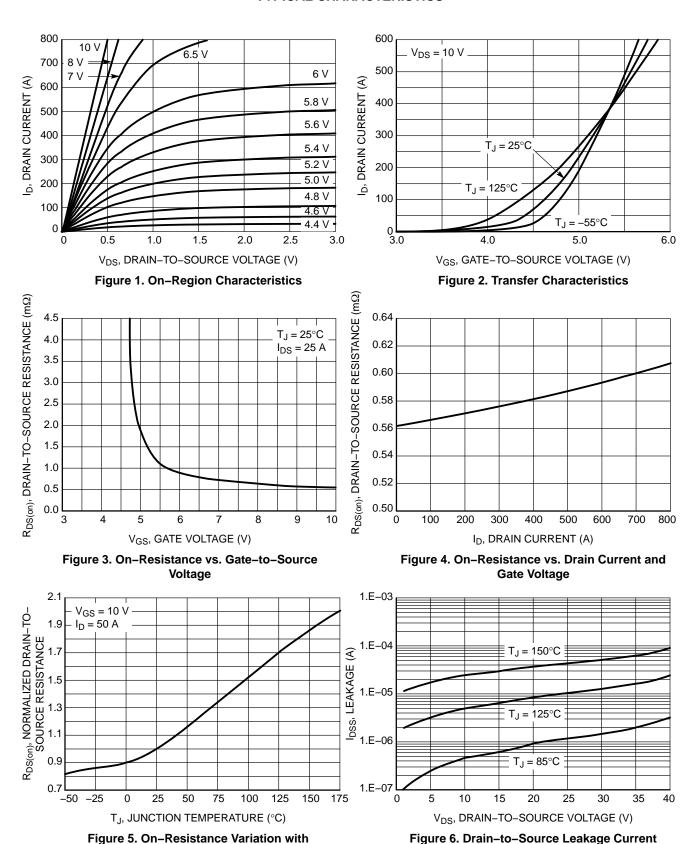
Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS				•	•	•	•
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /				19.7		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>					10	^
		$V_{DS} = 40 \text{ V}$	T <sub>J</sub> = 125°C			250	μΑ
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = 20 V				100	nA
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$		2.0		4.0	V
Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>				-6.2		mV/°C
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 50 A		0.57	0.7	mΩ
Forward Transconductance	9FS	V <sub>DS</sub> =15 V, I <sub>D</sub> = 50 A			210		S
CHARGES, CAPACITANCES & GATE RE	SISTANCE						
Input Capacitance	C <sub>ISS</sub>	$V_{GS} = 0 \text{ V, f} = 1 \text{ MHz, V}_{DS} = 25 \text{ V}$			8400		pF
Output Capacitance	C <sub>OSS</sub>				4600		
Reverse Transfer Capacitance	C <sub>RSS</sub>				120		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 20 V; I <sub>D</sub> = 50 A			128		
Threshold Gate Charge	Q <sub>G(TH)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 20 V; I <sub>D</sub> = 50 A			22		nC
Gate-to-Source Charge	Q <sub>GS</sub>				35		
Gate-to-Drain Charge	$Q_{GD}$				26		
Plateau Voltage	$V_{GP}$				4.3		V
SWITCHING CHARACTERISTICS (Note 5	5)						
Turn-On Delay Time	t <sub>d(ON)</sub>	$V_{GS}$ = 10 V, $V_{DS}$ = 20 V, $I_{D}$ = 50 A, $R_{G}$ = 2.5 $\Omega$			16		- ns
Rise Time	t <sub>r</sub>				113		
Turn-Off Delay Time	t <sub>d(OFF)</sub>				77		
Fall Time	t <sub>f</sub>				109		
DRAIN-SOURCE DIODE CHARACTERIS	STICS			•		•	•
Forward Diode Voltage V <sub>SD</sub>	V <sub>SD</sub>	$V_{GS} = 0 \text{ V},$ $I_{S} = 50 \text{ A}$	$T_J = 25^{\circ}C$		0.76	1.2	V
			T <sub>J</sub> = 125°C		0.63		
Reverse Recovery Time	t <sub>RR</sub>	$V_{GS} = 0 \text{ V, dIS/dt} = 100 \text{ A/}\mu\text{s,}$ $I_{S} = 50 \text{ A}$			96		ns
Charge Time	t <sub>a</sub>				49		
Discharge Time	t <sub>b</sub>				47		
Reverse Recovery Charge	Q <sub>RR</sub>				189		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width  $\leq 300~\mu s$ , duty cycle  $\leq 2\%$ .

5. Switching characteristics are independent of operating junction temperatures.

#### **TYPICAL CHARACTERISTICS**



vs. Voltage

**Temperature** 

#### **TYPICAL CHARACTERISTICS**

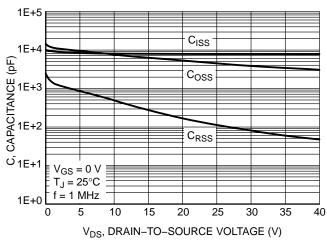


Figure 7. Capacitance Variation

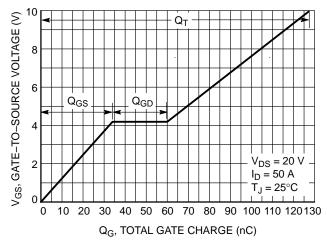


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

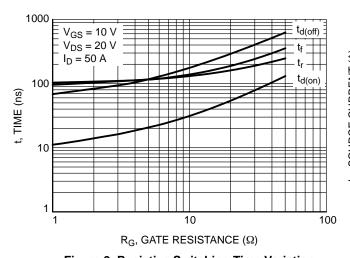


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

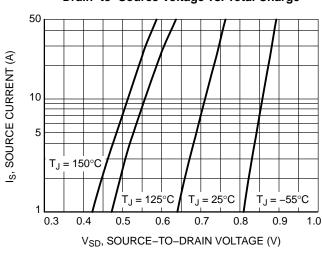


Figure 10. Diode Forward Voltage vs. Current

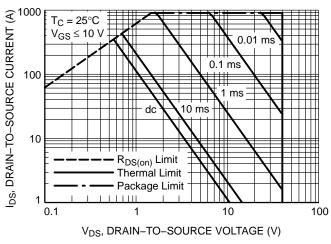


Figure 11. Safe Operating Area

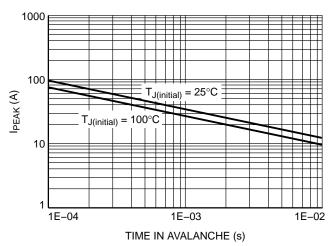


Figure 12. I<sub>PEAK</sub> vs. Time in Avalanche

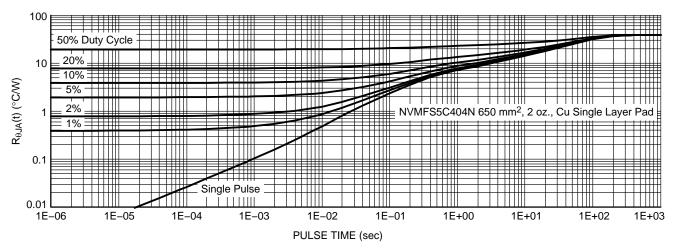


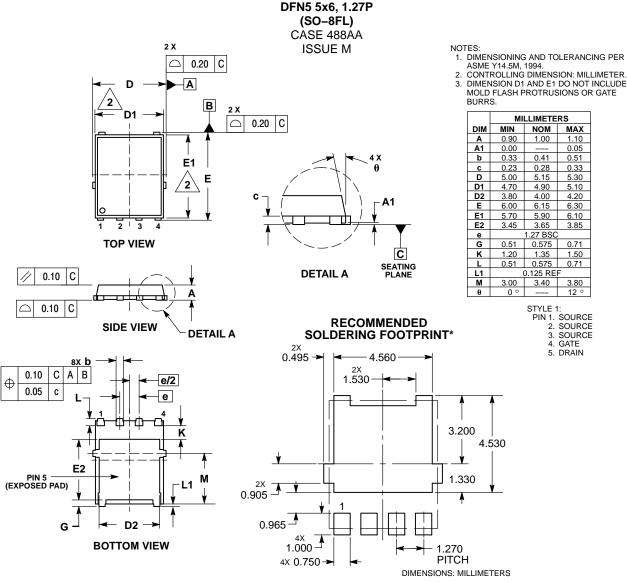
Figure 13. Thermal Characteristics

## **DEVICE ORDERING INFORMATION**

Device	Device Marking		Shipping <sup>†</sup>		
NVMFS5C404NT1G	5C404N	DFN5 (Pb-Free)	1500 / Tape & Reel		
NVMFS5C404NWFT1G	404NWF	DFN5 (Pb-Free, Wettable Flanks)	1500 / Tape & Reel		
NVMFS5C404NT3G	5C404N	DFN5 (Pb-Free)	5000 / Tape & Reel		
NVMFS5C404NWFT3G	404NWF	DFN5 (Pb-Free, Wettable Flanks)	5000 / Tape & Reel		
NVMFS5C404NAFT1G	5C404N	DFN5 (Pb-Free)	1500 / Tape & Reel		
NVMFS5C404NWFAFT1G	404NWF	DFN5 (Pb-Free, Wettable Flanks)	1500 / Tape & Reel		

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### PACKAGE DIMENSIONS



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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